

**KSA910**

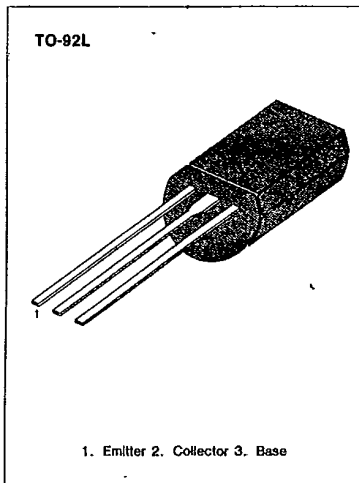
**PNP EPITAXIAL SILICON TRANSISTOR**

**DRIVER STAGE AUDIO AMPLIFIER  
HIGH VOLTAGE SWITCHING APPLICATIONS**

- Complement to KSC2310
- Collector-Emitter Voltage  $V_{CE0} = -150V$
- Output Capacitance:  $C_{ob} = 5pF$  (MAX)

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	- 150	V
Collector-Emitter Voltage	$V_{CEO}$	- 150	V
Emitter-Base Voltage	$V_{EBO}$	- 5	V
Collector Current	$I_C$	- 50	mA
Collector Dissipation	$P_C$	800	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 ~ +150	$^\circ C$



**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = -100\mu A, I_E = 0$	- 150			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = -5mA, I_B = 0$	- 150			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = -10\mu A, I_C = 0$	- 5			V
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = -150V, I_E = 0$			- 100	nA
DC Current Gain	$h_{FE}$	$V_{CE} = -5V, I_C = -10mA$	40		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			- 0.8	V
Current-Gain-Bandwidth Product	$f_T$	$V_{CE} = -30V, I_C = -10mA$		100		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_C = 0, f = 1MHz$			5.0	pF

**$h_{FE}$  CLASSIFICATION**

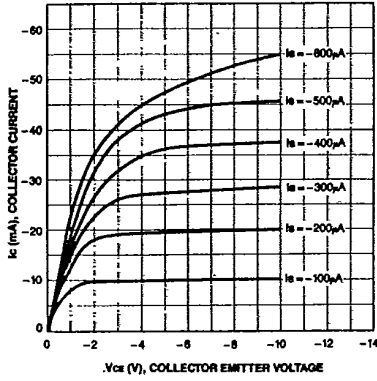
Classification	R	O	Y
$h_{FE}$	40-80	70-140	120-240

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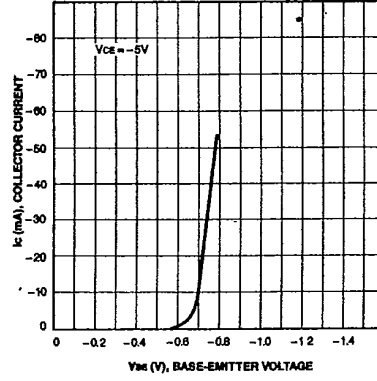
PNP EPITAXIAL SILICON TRANSISTOR

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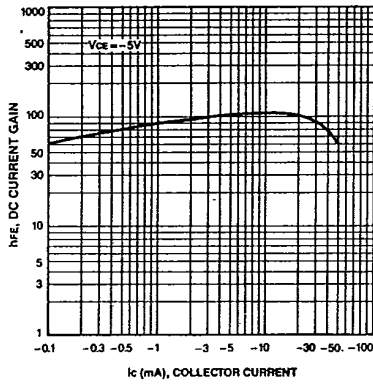
STATIC CHARACTERISTIC



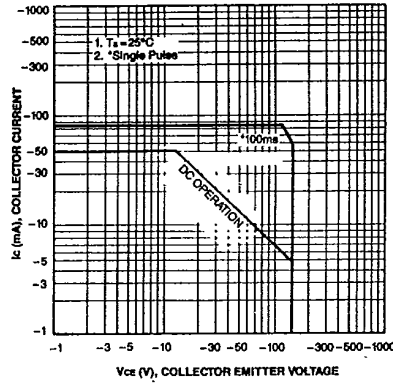
BASE-EMITTER ON VOLTAGE



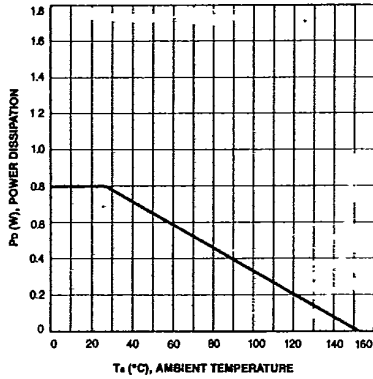
DC CURRENT GAIN



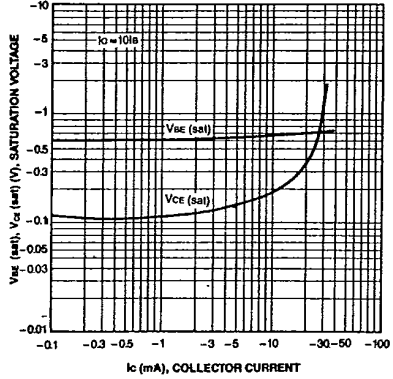
SAFE OPERATING AREA



POWER DERATING



COLLECTOR-EMITTER SATURATION VOLTAGE. BASE-EMITTER SATURATION VOLTAGE.



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